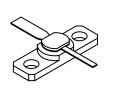
# The RF Line Microwave Power Transistors

... designed primarily for large–signal output and driver amplifier stages in the 1.5 to 3.0 GHz frequency range.

- Designed for Class B or C, Common Base Linear Power Amplifiers
- Specified 28 Volt, 3.0 GHz Characteristics: Output Power — 1.0 to 5.0 Watts Power Gain — 5.0 to 7.0 dB Min Collector Efficiency — 30% Min
- Gold Metallization for Improved Reliability
- Diffused Ballast Resistors
- Circuit board photomaster available upon request by contacting RF Tactical Marketing in Phoenix, AZ.

# MRW3001 MRW3003 MRW3005

5.0-7.0 dB 1.5-3.0 GHz 1.0-5.0 WATTS MICROWAVE POWER TRANSISTORS



CASE 328A-03, STYLE 1 (GP-13) MRW3001, 3003, 3005

# MAXIMUM RATINGS

Rating	Symbol	3001	3003	3005	Unit
Collector–Base Voltage	VCBO	45			Vdc
Emitter–Base Voltage	VEBO	3.5			Vdc
Operating Junction Temperature	Тj	200			°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +200			°C

#### THERMAL CHARACTERISTICS

Characteristic	Symbol	Max			Unit
Thermal Resistance, RF, Junction to Case	R <sub>θ</sub> JC	35	17	8.5	°C/W

# **ELECTRICAL CHARACTERISTICS** ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic		Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS						
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 10 mA, V <sub>BE</sub> = 0) (I <sub>C</sub> = 30 mA, V <sub>BE</sub> = 0) (I <sub>C</sub> = 50 mA, V <sub>BE</sub> = 0)	MRW3001 MRW3003 MRW3005	V <sub>(BR)</sub> CES	50 50 50			Vdc
Collector–Base Breakdown Voltage ( $I_C = 1.0 \text{ mA}, I_E = 0$ ) ( $I_C = 3.0 \text{ mA}, I_E = 0$ ) ( $I_C = 5.0 \text{ mA}, I_E = 0$ )	MRW3001 MRW3003 MRW3005	V <sub>(BR)</sub> CBO	45 45 45			Vdc
Emitter–Base Breakdown Voltage $(I_E = 1.0 \text{ mA}, I_C = 0)$		V <sub>(BR)EBO</sub>	3.5	—	-	Vdc
Collector Cutoff Current ( $V_{CB} = 28 V, I_E = 0$ )	MRW3001 MRW3003 MRW3005	ІСВО			0.5 0.75 1.25	mAdc
ON CHARACTERISTICS						
DC Current Gain (I <sub>C</sub> = 100 mA, V <sub>CE</sub> = 5.0 V) (I <sub>C</sub> = 300 mA, V <sub>CE</sub> = 5.0 V) (I <sub>C</sub> = 500 mA, V <sub>CE</sub> = 5.0 V)	MRW3001 MRW3003 MRW3005	hFE	10 10 10		120 120 120	_

(continued)



### **ELECTRICAL CHARACTERISTICS** — continued ( $T_C = 25^{\circ}C$ unless otherwise noted.)

Characteristic		Symbol	Min	Тур	Max	Unit
DYNAMIC CHARACTERISTICS						
Output Capacitance ( $V_{CB}$ = 28 V, I <sub>E</sub> = 0, f = 1.0 MHz)	MRW3001 MRW3003 MRW3005	C <sub>ob</sub>		3.5 5.7 8.4	4.0 7.0 10	pF
FUNCTIONAL TESTS						
Common–Base Amplifier Power Gain ( $V_{CE} = 28 \text{ V}, P_{Out} = 1.0 \text{ W}, f = 3.0 \text{ GHz}$ ) ( $V_{CE} = 28 \text{ V}, P_{Out} = 3.0 \text{ W}, f = 3.0 \text{ GHz}$ ) ( $V_{CE} = 28 \text{ V}, P_{Out} = 5.0 \text{ W}, f = 3.0 \text{ GHz}$ )	MRW3001 MRW3003 MRW3005	G <sub>PB</sub>	7.0 6.0 5.0	  	 	dB
Collector Efficiency (V <sub>CE</sub> = 28 V, P <sub>out</sub> = 1.0 W, f = 3.0 GHz) (V <sub>CE</sub> = 28 V, P <sub>out</sub> = 3.0 W, f = 3.0 GHz) (V <sub>CE</sub> = 28 V, P <sub>out</sub> = 5.0 W, f = 3.0 GHz)	MRW3001 MRW3003 MRW3005	ης	30 30 30			%
Load Mismatch ( $V_{CE} = 28 \text{ V}, \text{ f} = 3.0 \text{ GHz}, \text{ Load VSWR} = \infty:1, \text{ A}$ $P_{out} = 1.0 \text{ W}$ $P_{out} = 3.0 \text{ W}$ $P_{out} = 5.0 \text{ W}$	All Phase Angles) MRW3001 MRW3003 MRW3005	Ψ	No Degradation in Output Power			

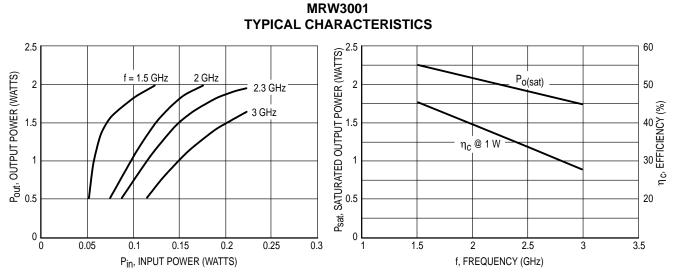


Figure 1. Output Power versus Input Power



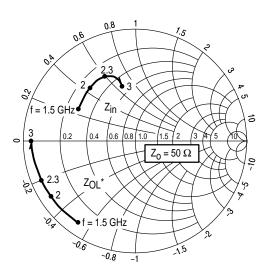


Figure 3. Series Equivalent Input/Output Impedance

# MRW3003 TYPICAL CHARACTERISTICS

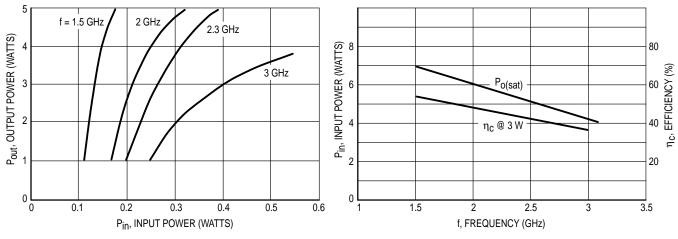




Figure 5. Psat and  $\eta$  versus Frequency

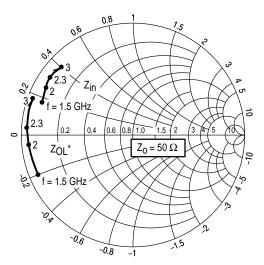


Figure 6. Series Equivalent Input/Output Impedance

# MRW3005 TYPICAL CHARACTERISTICS

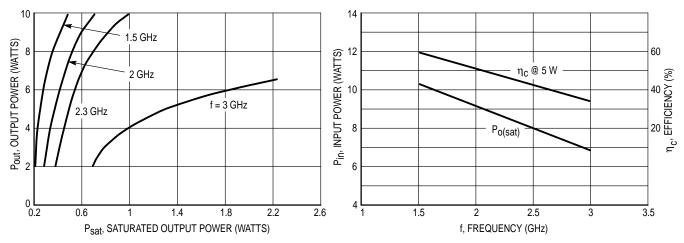




Figure 8. P<sub>sat</sub> and  $\eta$  versus Frequency

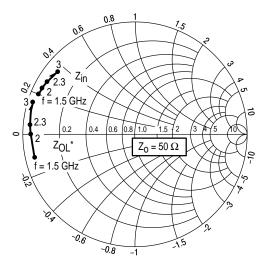
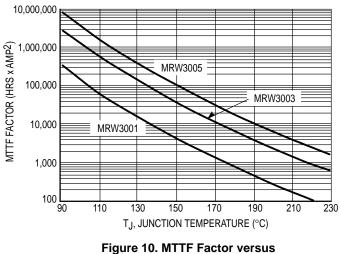


Figure 9. Series Equivalent Input/Output Impedance



Junction Temperature

### MTTF Factor (Normalized to 1.0 ampere<sup>2</sup> Continuous Duty)

The graph shown displays MTTF in hours x ampere<sup>2</sup> emitter current for each of the 3.0 GHz devices. Life tests at elevated temperatures have correlated to better than  $\pm 10\%$  to the theoretical prediction for metal failure. **CAUTION** — A calculation is required to obtain actual metal life. Sample MTTF calculations based on operating conditions are shown below.

#### Junction Temperature — °C

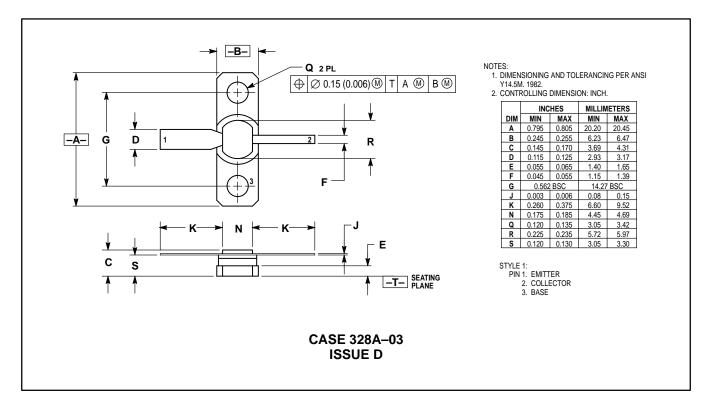
To calculate metal lifetime under any set of conditions, obtain actual data or estimate from typical performance curves. Solve for T<sub>J</sub> (°C):

(1) 
$$T_J = \theta_{JF} \left( \frac{P_{out} \times 100}{\eta_c \%} + P_{in} - P_{out} \right) + TFLANGE$$

Enter graph of MTF factor versus TJ. Obtain MTF factor. Calculate metal life by:

(2) Metal Life in Hours =  $\frac{\text{MTF Factor}}{\text{I}\text{C}^2 \text{ (Amps)}}$ 

# PACKAGE DIMENSIONS



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